

5V to 100V Input, 2A Asynchronous Buck Converter

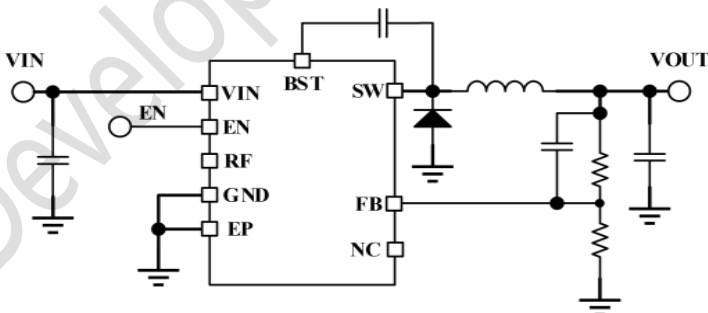
FEATURES

- Input Voltage Range: 5V to 100V
- Peak and valley current limit protection
- Continuous Output Current: 2A
- Adjustable switching frequency
- Reference Voltage: 1.2V \pm 1.5% @25°C
- Integrated high-side MOSFET:325mΩ
- Low Quiescent Current: 350μA
- Low Shutdown Current: 5μA
- EN UVLO and thermal shutdown protection
- Optional Operation Modes at Light-Load
- Internal VCC bias regulator and boot diode
- Over Current Protection
- Fixed 3ms Internal soft start timer
- Short Protection with Hiccup-Mode
- Thermal Shutdown Protection
- ESOP8 package

APPLICATIONS

- High-cell-count battery packs (E-Bike, E-Scooter)
- POE
- Appliances, power and garden tools
- Motor drives, drones, telecom
- Industrial Automation and Motor Control
- USB Dedicated Charging Ports and Battery Chargers
- Vehicle Accessories: GPS, Entertainment

TYPICAL APPLICATION CIRCUIT



DESCRIPTIONS

The DP312102ASO asynchronous buck converter is designed to regulate over a wide input voltage range, minimizing the need for external surge suppression components. A minimum controllable on time of 100ns facilitates large step down conversion ratios, enabling the direct step down from a 48V nominal input to low-voltage rails for reduced system complexity and solution cost. The DP312102ASO operates during input voltage dips as low as 5V, at nearly 100% duty cycle if needed, making it an excellent choice for wide input supply range industrial and high cell count battery pack applications.

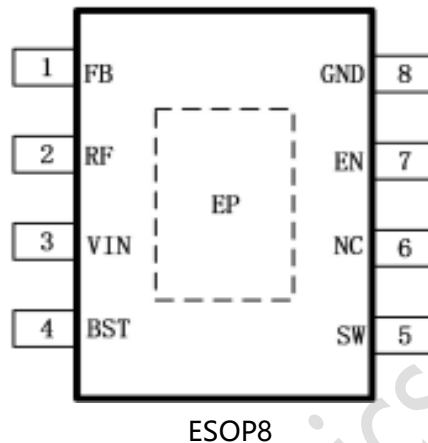
With integrated high side power MOSFET, the DP312102ASO delivers up to 2A of output current. A constant on time (COT) control architecture provides nearly constant switching frequency with excellent load and line transient response. Additional features of the DP312102ASO include ultra low IQ and high light load efficiency, innovative peak and valley over current protection, integrated VCC bias supply and bootstrap diode, precision enable and input UVLO, and thermal shutdown protection with automatic recovery.

ORDERING INFORMATION

Part Number	Description
ESOP8	Pb free in T&R, 4000 Pcs/Reel

PRODUCT DESCRIPTION

➤ Pin Arrangement

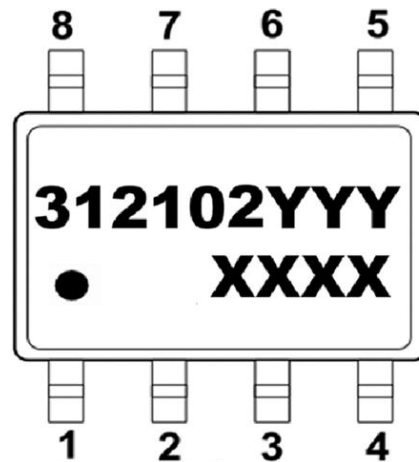


➤ Pin Configuration

ESOP8	Pin Name	Description
1	FB	Feedback input of voltage regulation comparator.
2	RF	On time programming pin. A resistor between this pin and GND sets the buck switch on Time. Floating this pin Fixed frequency of 300KHz.
3	VIN	Regulator supply input pin to high side power MOSFET and internal bias regulator. Connect directly to the input supply of the buck converter with short, low impedance paths.
4	BST	Supply input for the high-side NFET gate drive circuit. Connect a 0.1 μ F capacitor between VBST and SW pins.
5	SW	Switching node that is internally connected to the source of the high side NMOS buck switch and the drain of the low side NMOS synchronous rectifier. Connect to the switching node of the power inductor.
6	NC	No Connect
7	EN/UVLO	Precision enable and under voltage lockout (UVLO) programming pin. If the EN/UVLO voltage is below 1.1V, the converter is in the shutdown mode with all functions disabled. If the UVLO voltage is greater than 1.1V and below 1.5V, the converter is in standby mode with the internal VCC regulator operational and no switching. If the EN/UVLO voltage is above 1.5V, the start up sequence begins. This pin has an internal pull up 10M ohm resistor to make sure IC work when EN pin is float.

8	GND	Ground Pin
9	EP	Exposed pad of the package. No internal electrical connection. Solder the EP to the GND pin and connect to a large copper plane to reduce thermal resistance.

➤ Marking Information



DP312102 for product name:

YYY refers to the following table description, represents different packaging and special functions

XXXX The first X represents the last year, 2020 is 0; The second X represents the month, in A-L 12 letters; The third and fourth X on behalf of the date, 01-31 said;

Marking	Model	Description
312102A	DP312102ASO	DP312102ASO Buck Converter, 5V~100V, 2A, VFB 1.2V, ESOP8

➤ Absolute Maximum Ratings

PARAMETER	Min	Max	Unit
VIN Voltage	-0.3	100	V
EN Voltage	-0.3	100	V
SW Voltage(DC)	-0.3	100	V
SW Voltage(AC less than 10ns while Switching)	-1.5	100	V
FB Voltage	-0.3	5.5	V
BS Voltage(vs SW)	-0.3	5.5	V
Operating junction temperature,TJ	-40	150	°C
Storage temperature, Tstg	-65	150	°C
Lead Temperature (Soldering, 10sec.)	-	260	°C

Over operating temperature range (unless otherwise noted)(1)

Note:(1)Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal

➤ Recommended Operating Conditions

PARAMETER	Min	Max	Unit
VIN Voltage(V _{IN})	5	100	V
Output current	0	2	A
TJ	-40	125	°C

Note : (1)All limits specified at room temperature (TA = 25°C) unless otherwise specified. All room temperature limits are 100% production tested. All limits at temperature extremes are ensured through correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

ESD Ratings

PARAMETER	Description	Value	Unit
HBM	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
CDM	Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±200	V

Note : (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

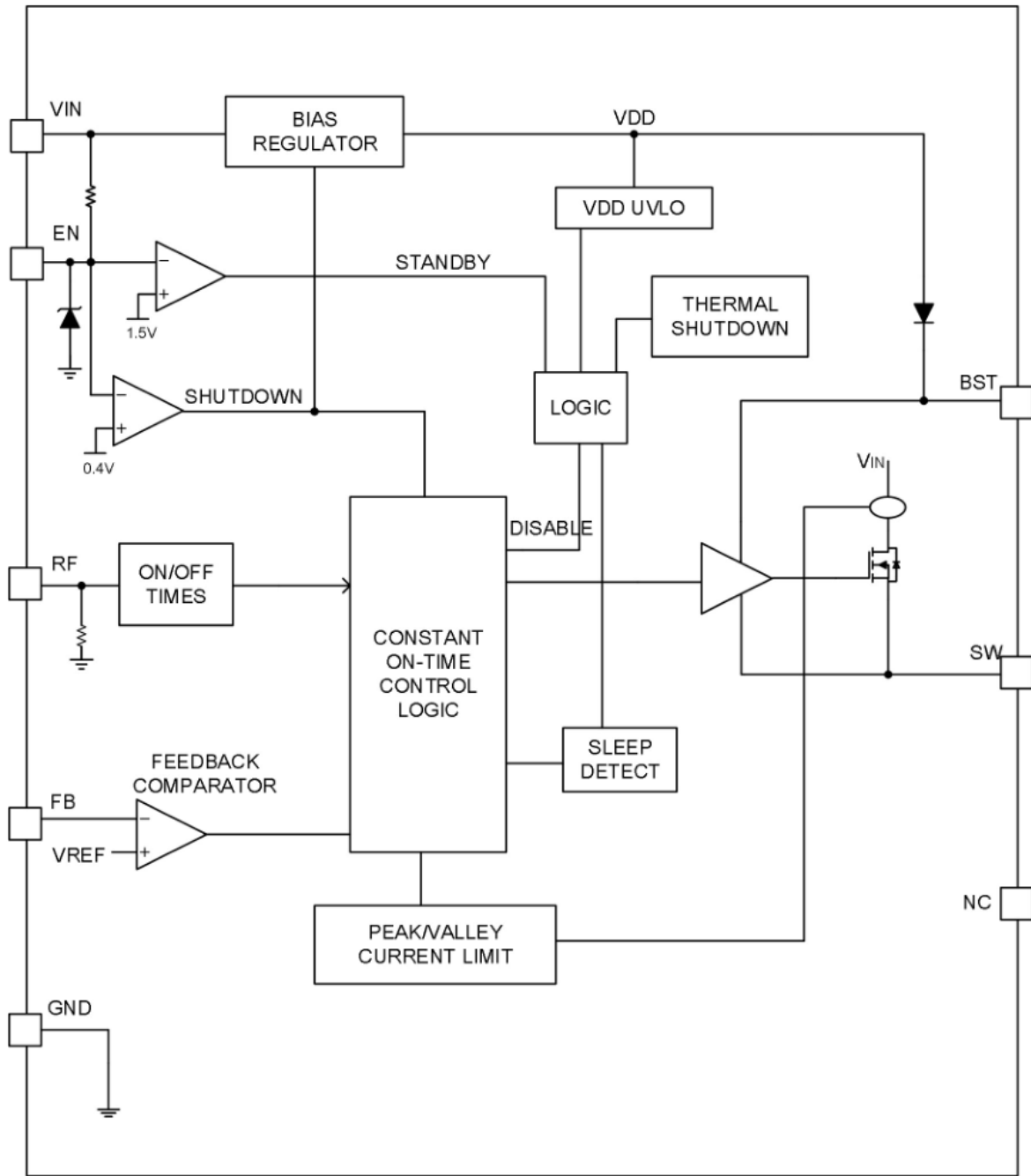
➤ Thermal Information

THERMAL METRIC	Description	ESOP8	Unit
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾	41.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	37.3	°C/W
$R_{\theta JB}$	Junction-to-board(Bottom) thermal resistance	25.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	8.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	25.2	°C/W

Note (1): The package thermal impedance is calculated in accordance to JESD 51-7.

Note (2): Thermal Resistances were simulated on a 4-layer, JEDEC board

BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS

(Typical at $V_{in}=24V$, $V_{EN}=2V$, $T_J=25^{\circ}C$, unless otherwise noted.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Input Voltage	V_{IN}		5		100	V
V_{IN} Quiescent Current	I_Q	No-switching, $V_{FB}=1.3V$		330	400	μA
Shutdown Current	I_{SHDN}	$V_{EN}=0V$		5	10	μA
FB Voltage	V_{FB}	$T_J=25^{\circ}C$	1.18	1.2	1.218	V
Switching Frequency	F_{SW}	$R_{rf}=NC$		300		KHZ
		$R_{rf}=200K\Omega$		500		KHZ
Current Limit Threshold	$I_{HS(OC)}$			4	4.15	A
High-Side MOS ON-Resistance	$R_{DS(on)(HS)}$			325		$m\Omega$
EN Rising Threshold	$V_{EN(R)}$	EN Rising	1.45	1.5	1.55	V
EN Falling Threshold	$V_{EN(F)}$	EN Falling	1.35	1.4	1.44	V
VSD-Rising	VSD-Rising	EN Rising			1.1	V
VSD-Falling	VSD-Falling	EN Falling	0.45			V
Gate Driver UVLO	V_{bst-UV}	V_{bst} Rising		2.7	3.4	V
Soft Start	T_{SS}	10%* V_{out} to 90%* V_{out}	1.75	3	4.75	ms
Over-Temperature Protection	T_{SD}			175		$^{\circ}C$
Over-Temperature Protection hysteresis	ΔT_{SD}			10		$^{\circ}C$

TYPICAL CHARACTERISTICS

Test Condition: TA = 25°C, VIN=48V, Vout=12V, unless otherwise noted.

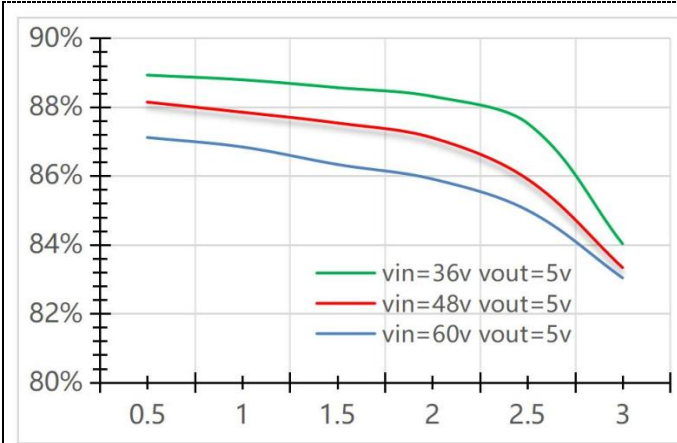


Figure1 5V Output Efficiency

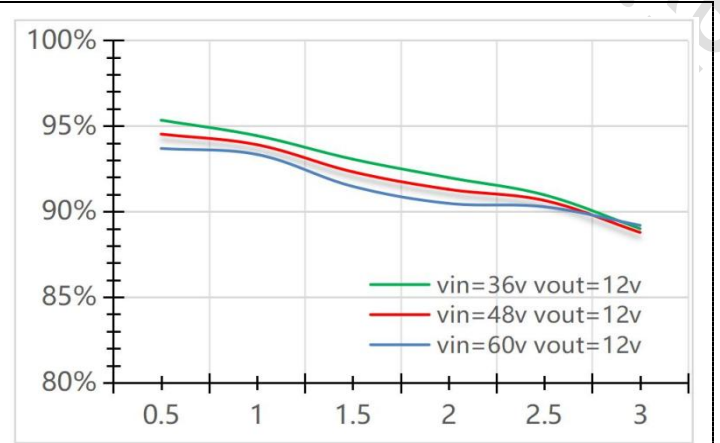


Figure2 12V Output Efficiency

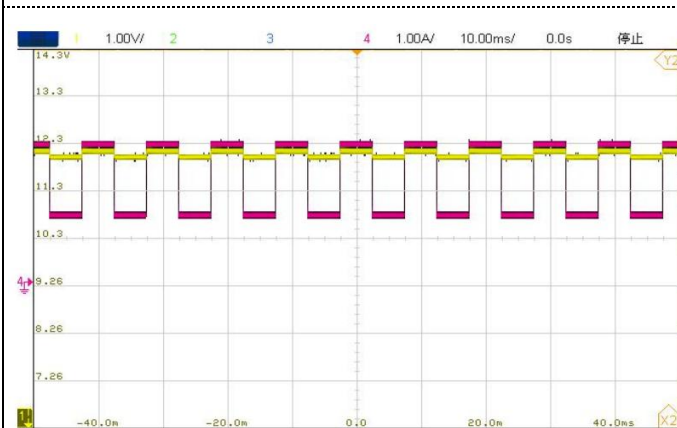


Figure3 12V Load Transient 100HZ 1.5A-3A 0.25A/us

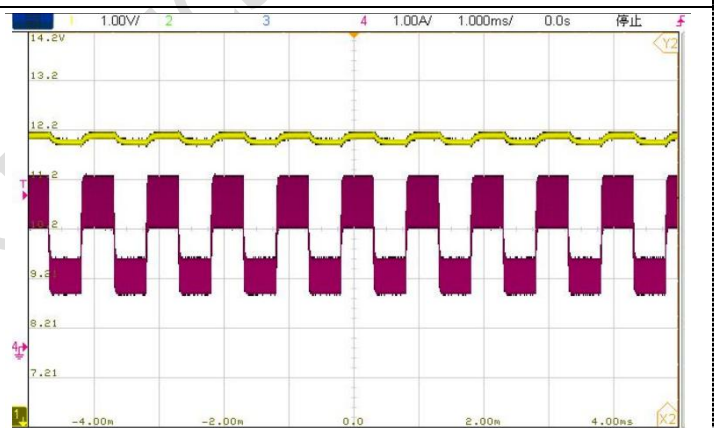
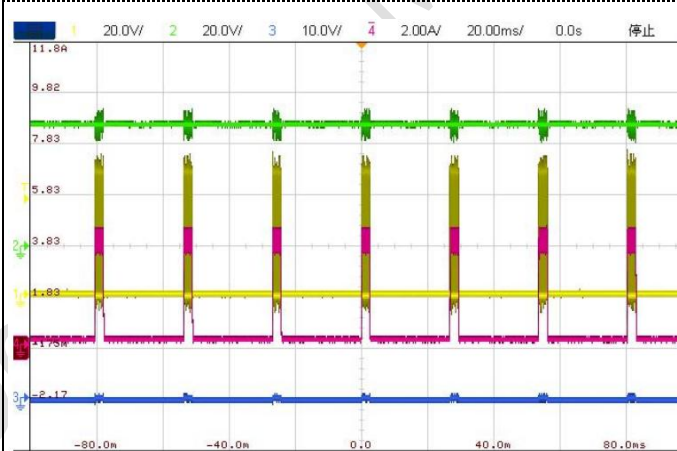
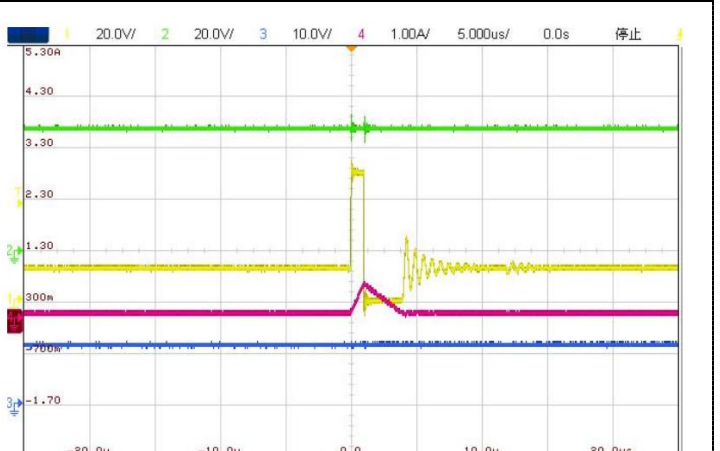


Figure4 12V Load Transient 1KHZ 1.5A-3A 0.25A/us



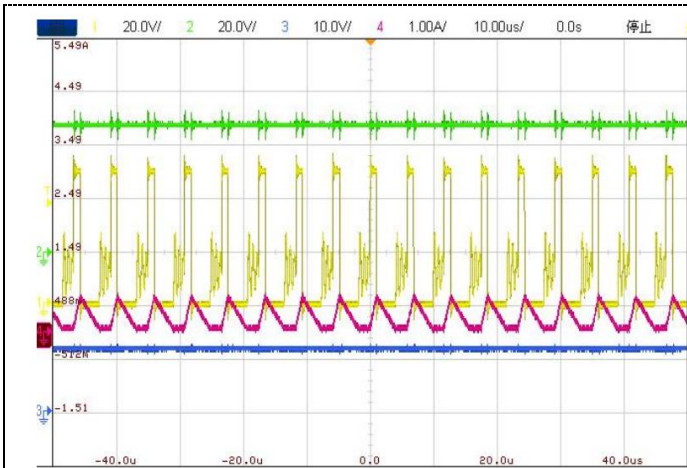
CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure5 Short Circuit waveform



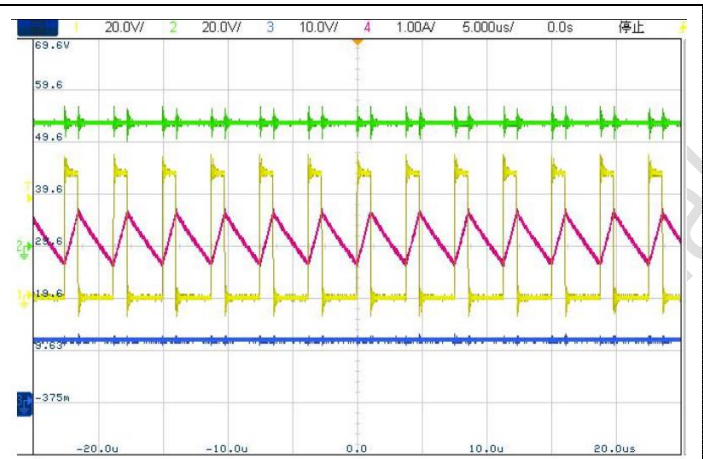
CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure6 DCM with Iout=0.1A



CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure7 DCM with Iout=0.2A



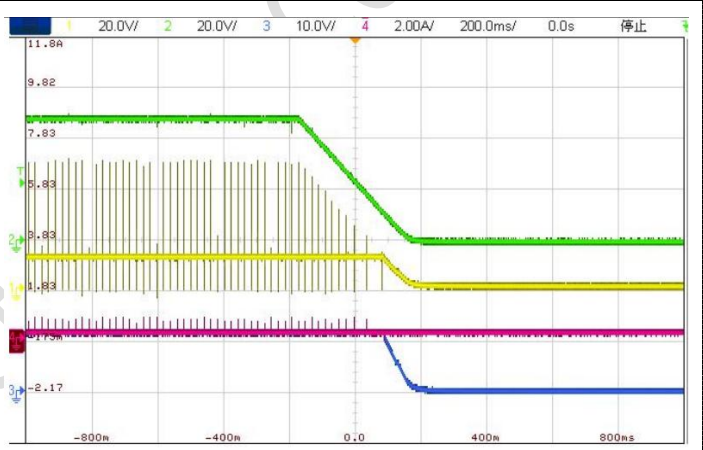
CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure8 CCM with Iout=3A



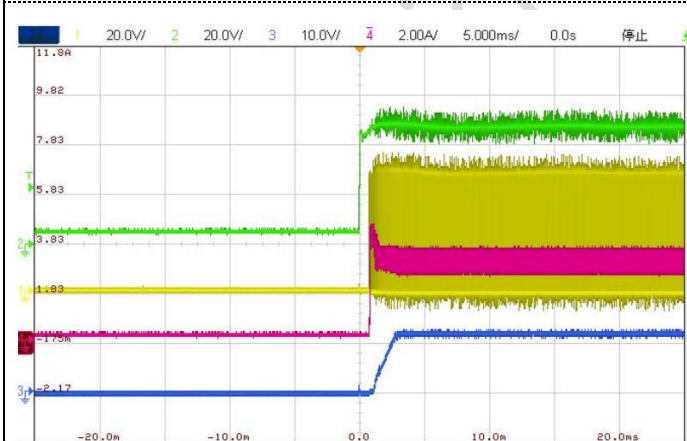
CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure9 VIN StartUp with No Load



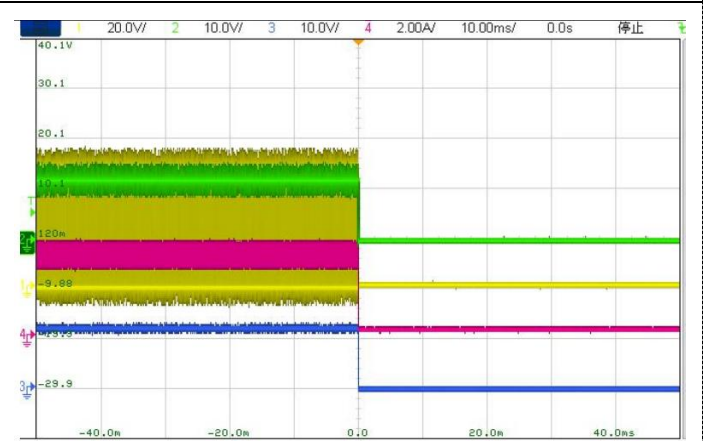
CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure10 ShutDown with No Load



CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure11 VIN StartUp with 3A Load



CH1:SW CH2:VIN CH3:Vout CH4:IL

Figure12 VIN ShutDown with 3A Load

➤ Control Architecture

The DP312102ASO step down switching converter employs a constant on time (COT) control scheme. The COT control scheme sets a fixed on time t_{ON} of the high side FET using a timing resistor (R_{ON}). The t_{ON} is adjusted as V_{in} changes and is inversely proportion to input voltage to maintain a fixed frequency when in continuous conduction mode (CCM). After expiration of t_{ON} , the high side FET remains off until the feedback pin is equal or below the reference voltage of 1.2V. In order to maintain stability, the feedback comparator requires a minimal ripple voltage that is in phase with the inductor current during the off time. Furthermore, this change in feedback voltage during the off time must be large enough to dominate any noise present at the feedback node. The minimum recommended ripple voltage is 20mV. Refer to Table for different types of ripple injection schemes that ensure stability over the full input voltage range. During a rapid start up or a positive load step, the regulator operates with minimum off times until regulation is achieved. This feature enables extremely fast load transient response with minimum output voltage undershoot. When regulating the output in steady state operation, the off time automatically adjusts itself to produce the SW pin duty cycle required for output voltage regulation to maintain a fixed switching frequency.

Ripple Generation Methods

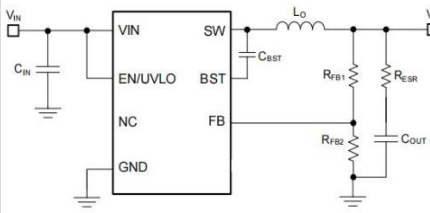
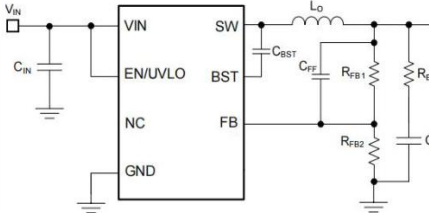
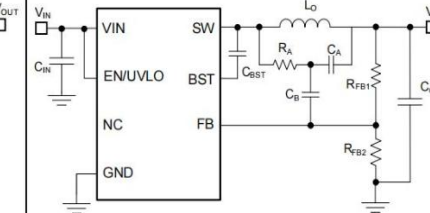
TYPE 1	TYPE 2	TYPE 3
Lowest Cost	Reduced Ripple	Minimum Ripple
		
$R_{ESR} \geq \frac{20\text{mV} \cdot V_{OUT}}{V_{FB1} \cdot \Delta I_{L(nom)}}$ $R_{ESR} \geq \frac{V_{OUT}}{2 \cdot V_{IN} \cdot F_{SW} \cdot C_{OUT}}$	$R_{ESR} \geq \frac{20\text{mV}}{\Delta I_{L(nom)}}$ $R_{ESR} \geq \frac{V_{OUT}}{2 \cdot V_{IN} \cdot F_{SW} \cdot C_{OUT}}$ $C_{FF} \geq \frac{1}{2\pi \cdot F_{SW} \cdot (R_{FB1} \parallel R_{FB2})}$	$C_A \geq \frac{10}{F_{SW} \cdot (R_{FB1} \parallel R_{FB2})} \quad (3)$ $R_A C_A \leq \frac{(V_{IN-nom} - V_{OUT}) \cdot t_{ON} (@V_{IN-nom})}{20\text{mV}} \quad (4)$ $C_B \geq \frac{t_{TR-settling}}{3 \cdot R_{FB1}} \quad (5)$

Table presents 3 different methods for generating appropriate voltage ripple at the feedback node. Type-1 ripple generation method uses a single resistor, R_{ESR} in series with the output capacitor. The generated voltage ripple has two components, capacitive ripple caused by the inductor ripple current charging and discharging the output capacitor and resistive ripple caused by the inductor ripple current flowing into the output capacitor and through series resistance R_{ESR} . The capacitive ripple component is out of phase with the inductor current and does not decrease monotonically during the off time. The resistive ripple component is in phase with the inductor current and decreases monotonically during the off time. The resistive ripple



must exceed the capacitive ripple at VOUT for stable operation. If this condition is not satisfied, unstable switching behavior is observed in COT converters, with multiple on time bursts in close succession followed by a long off time. **Equation 1** and **Equation 2** define the value of the series resistance RESR to ensure sufficient in phase ripple at the feedback node.

Type-2 ripple generation uses a CFF capacitor in addition to the series resistor. As the output voltage ripple is directly AC coupled by CFF to the feedback node, the RESR and ultimately the output voltage ripple are reduced by a factor of V_{OUT} / V_{FB1} .

Type-3 ripple generation uses an RC network consisting of RA and CA, and the switch node voltage to generate a triangular ramp that is in phase with the inductor current. This triangular wave is the AC coupled into the feedback node with capacitor CB. Because this circuit does not use output voltage ripple, it is suited for applications where low output voltage ripple is critical.

FUNCTIONS DESCRIPTION

● Feature Description

The DP312102ASO is an easy to use, ultra low IQ constant on time (COT) asynchronous step down buck regulator. With integrated high side power MOSFET, the DP312102ASO is a low cost, highly efficient buck converter that operates from a wide input voltage of 5V to 100V, delivering up to 2A DC load current. The DP312102ASO is available in the ESOP8 package. This constant on time (COT) converter is ideal for low noise, high current, and fast load transient requirements, operating with a predictive on time switching pulse. Over the input voltage range, input voltage feed forward is employed to achieve a quasi fixed switching frequency. A controllable on time as low as 100ns permits high step down ratios and a minimum forced off time of 200ns provides extremely high duty cycles allowing VIN to drop close to VOUT before frequency fold back occurs. At light loads the device transitions into an ultra low IQ mode to maintain high efficiency and prevent draining battery cells connected to the input when the system is in standby. The DP312102ASO implements a smart peak and valley current limit detection circuit to ensure robust protection during output short circuit conditions. Control loop compensation is not required for this regulator, reducing design time and external component count. The DP312102ASO incorporates additional features for comprehensive system requirements, including an open drain Power Good circuit for power rail sequencing and fault reporting, internally fixed soft start, monotonic start up into prebiased loads, smart cycle by cycle current limit for optimal inductor sizing, and thermal shutdown with automatic recovery. These features enable a flexible and easy to use platform for a wide range of applications. The DP312102ASO supports a wide range of end equipment systems requiring a regulated output from a high input supply where the transient voltage deviates from its DC level. Examples of such end equipment systems are 48V automotive systems, high cell count battery pack systems, 24V industrial

systems, and 48V telecom and PoE voltage ranges. The pin arrangement is designed for a simple layout requiring only a few external components.

● Internal VCC Regulator and Bootstrap Capacitor

The DP312102ASO contains an internal linear regulator that is powered from VIN with a nominal output of 5V, eliminating the need for an external capacitor to stabilize the linear regulator. The internal VCC regulator supplies current to internal circuit blocks including FET driver and logic circuits. The input pin (VIN) can be connected directly to line voltages up to 100V. As the power MOSFET has a low total gate charge, use a low bootstrap capacitor value to reduce the stress on the internal regulator. It is required to select a high quality 10nF 50V X7R ceramic bootstrap capacitor as specified in the Absolute Maximum Ratings. Selecting a higher value capacitance stresses the internal VCC regulator and damages the device. A lower capacitance than required may not be sufficient to drive the internal gate of the power MOSFET. An internal diode connects from the linear regulator to the BST pin to replenish the charge in the high side gate drive bootstrap capacitor when the SW voltage is low

● Soft Start

The DP312102ASO employs an internal soft start control ramp that allows the output voltage to gradually reach a steady state operating point, thereby reducing start up stresses and current surges. The soft start feature produces a controlled, monotonic output voltage start up. The soft start time is internally set to 3ms.

● UNDER-VOLTAGE LOCKOUT (UVLO)

The DP312102ASO contains a dual level EN/UVLO circuit. When the EN/UVLO voltage is below 1.1V (typical), the converter is in a low current shutdown mode and the input quiescent current (IQ) is dropped down to 5 μ A. When the voltage is greater than 1.1V

but less than 1.5V (typical), the converter is in standby mode. In standby mode the internal bias regulator is active while the control circuit is disabled. When the voltage exceeds the rising threshold of 1.5V (typical), normal operation begins. Install a resistor divider from VIN to GND to set the minimum operating voltage of the regulator.

● Adjustable Switching Frequency

Determine the RRF resistor using Equation 2 to set a specific switching frequency in CCM.

$$F_{sw}(kHz) = \frac{100000}{RRF(K\Omega)} \quad (2)$$

● Overvoltage Protection

The DP312102ASO includes an internal junction temperature monitor to protect the device in the event of a higher than normal junction temperature. If the junction temperature exceeds 175°C (typical), thermal shutdown occurs to prevent further power dissipation and temperature rise. The DP312102ASO initiates a restart sequence when the junction temperature falls to 165°C, based on a typical thermal shutdown hysteresis of 10°C. This is a nonlatching protection, and, as such, the device cycles into and out of thermal shutdown if the fault persists..

APPLICATION INFORMATION

The output stage of Asynchronous buck converter is mainly composed of inductor and capacitors. By switching the internally integrated High Side power MOSFET, the energy is stored and transferred to the load, and the second-order LC filter is formed to smooth the switching node voltage so that the stable output DC voltage is obtained.

● Setting Output Voltage

The output voltage is set by FB voltage, which is divided by resistor (R1 & R2) from output node to Ground. That resistor with 1% or higher accuracy is preferred. The output voltage value is set by equation as below.

$$V_{OUT} = V_{FB} \times ((R1 + R2)/R2)$$



Vref is the internal reference voltage of DP312102ASO, 1.2V.

Table1 Recommend Component Selection Table

VOUT (V)	R1 (kΩ)	R2 (kΩ)	BS (uF)	D1	L1 (uH)	CIN (uF)	COU (uF)
5	31.6	10	0.1	SS5 10	33	22	44
12	91	10	0.1	SS5 10	33	22	44

● Inductor selection

An inductor is required to supply constant current to the load while being driven by the switched input voltage. The common value of the inductance is between 22uH to 33uH. A larger value inductor will result in less current ripple and lower output voltage ripple. However, the larger value inductor will have larger physical size, higher DC resistance, and/or lower saturation current. A good rule to calculate the inductance is to allow the peak-to-peak ripple current in the inductor to be approximately 30% of the maximum load current. At the same time, it is needed to make sure that the peak inductor current is below the inductor saturation current.

The inductance value can be calculated by:

$$L = \frac{V_{OUT}}{f_s \times \Delta I_L} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$

Where VOUT is the output voltage, VIN is the input voltage, fs is the switching frequency, and ΔL is the peak-to-peak inductor ripple current.

The maximum inductor peak current is:

$$I_{L(MAX)} = I_{LOAD} + \frac{\Delta I_L}{2}$$

The choice of which style inductor to use mainly depends on the price vs. size requirements and any EMI constraints.

Under light load conditions below 100mA, larger inductance is recommended for improved efficiency

● Input capacitors selection

The input current to the step-down converter is discontinuous, therefore a capacitor is required to supply the AC current to the converter. It is recommend to use low ESR capacitors to optimize the performance. Ceramic capacitor is preferred, but tantalum or low-ESR electrolytic capacitors may also meet the requirements. It is better to choose X5R or X7R dielectrics when using ceramic capacitors.

Since the input capacitor (CIN) absorbs the input switching current, a good ripple current rating is required for the capacitor. The RMS current in the input capacitor can be estimated by:

$$I_{CIN} = I_{load} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)}$$

The worst-case condition occurs at $V_{IN} = 2 \times V_{OUT}$, where:

$$I_{CIN} = \frac{I_{load}}{2}$$

For simplification, choose the input capacitor whose RMS current rating is greater than half of the maximum load current. When electrolytic or tantalum capacitors are used, a small, high quality ceramic capacitor, i.e. 0.1μF, should be placed as close to the IC as possible. When ceramic capacitors are used, make sure that they have enough capacitance to maintain voltage ripple at input. The input voltage ripple caused by capacitance can be estimated by:

$$\Delta V_{IN} = \frac{I_{load}}{f_s \times C_{IN}} \times \frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$

CIN is the input capacitance.

● Output capacitors selection

The output capacitor (COUT) is required to maintain the DC output voltage. Ceramic, tantalum, or low ESR electrolytic capacitors are recommended. Low ESR capacitors are preferred to keep the output voltage ripple low. The output voltage ripple can be estimated by:

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_s \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times \left(R_{ESR} + \frac{1}{8 \times f_s \times C_{OUT}}\right)$$

Where L is the inductor value, RESR is the equivalent series resistance (ESR) value of the output capacitor and COUT is the output capacitance value. In the case of ceramic capacitors, the impedance at the switching frequency is dominated by the capacitance. The output voltage ripple is mainly determined by the capacitance. For simplification, the output voltage ripple can be estimated by:

$$\Delta V_{OUT} = \frac{V_{OUT}}{8 \times f_s^2 \times L \times C_{OUT}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$

In the case of tantalum or electrolytic capacitors, the ESR dominates the impedance at the switching frequency. For simplification, the output ripple can be approximated to:

$$\Delta V_{OUT} = \frac{V_{OUT}}{f_s \times L} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \times R_{ESR}$$

The characteristics of the output capacitor also affect the stability of the regulation system. The DP31212S/FS can be optimized for a wide range of capacitance and ESR values.

● Bootstrap Capacitor Selection

The recommended capacitor is 0.1 μF and rated 16 V or higher. The bootstrap capacitor is located between the SW pin and the BOOT pin. The bootstrap capacitor must be a high-quality ceramic type with an

X7R or X5R grade dielectric for temperature stability.

● Schottky Diode Selection

The breakdown voltage rating of the diode is preferred to be 25% higher than the maximum input voltage. The current rating for the diode must be equal to the maximum output current for best reliability in most applications. In cases where the input voltage is much greater than the output voltage, the average diode current is lower. In this case it is possible to use a diode with a lower average current rating, approximately $(1-D) \times I_{OUT}$ however the peak current rating must be higher than the maximum load current. A 3-A rated diode is a good starting point.

$$I_D = I_{OUT} \times \left(1 - \frac{V_{OUT}}{V_{VIN}}\right)$$

● PCB Layout

PCB layout is a critical portion of good power supply design. The following guidelines will help users design a PCB with the best power conversion efficiency, thermal performance, and minimized EMI.

1. The feedback network, resistor R7 and R6, should be kept close to FB pin. Vout sense path

should stay away from noisy nodes, such as SW & BS signals and preferably through a layer on the other side of shielding layer.

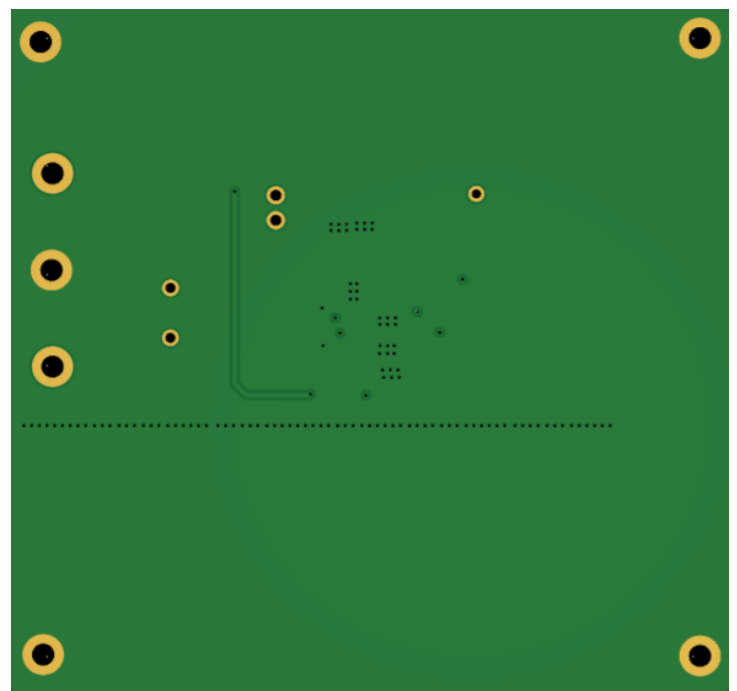
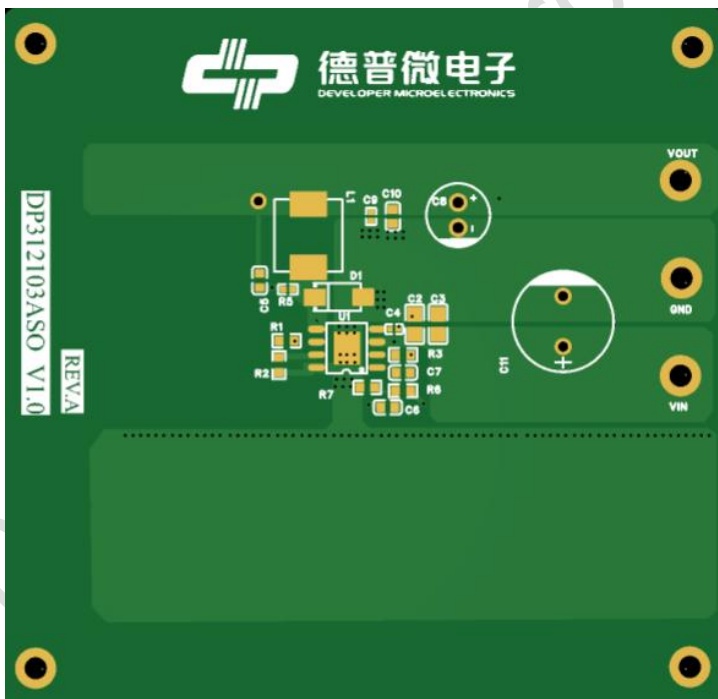
2. The input bypass capacitor C3 and C2 must be placed as close as possible to the VIN pin and ground. Grounding for both the input and output capacitors should consist of localized top side planes that connect to the GND pin and PAD. It is a good practice to place a ceramic cap near the VIN pin to reduce the high frequency injection current.

3. The inductor L should be placed close to the SW pin to reduce magnetic and electrostatic noise.

4. The output capacitor, COUT should be placed close to the junction of L and the diode D. The L, D, and COUT trace should be as short as possible to reduce conducted and radiated noise and increase overall efficiency.

5. The ground connection for C3, C2, C11 and C8, C9, C10 should be as small as possible and connect to system ground plane at only one spot (preferably at the COUT ground point) to minimize injecting noise into system ground plane.

6. Large GND Copper Pour near IC is recommended to minimize the heat of IC.





APPLICATION Example

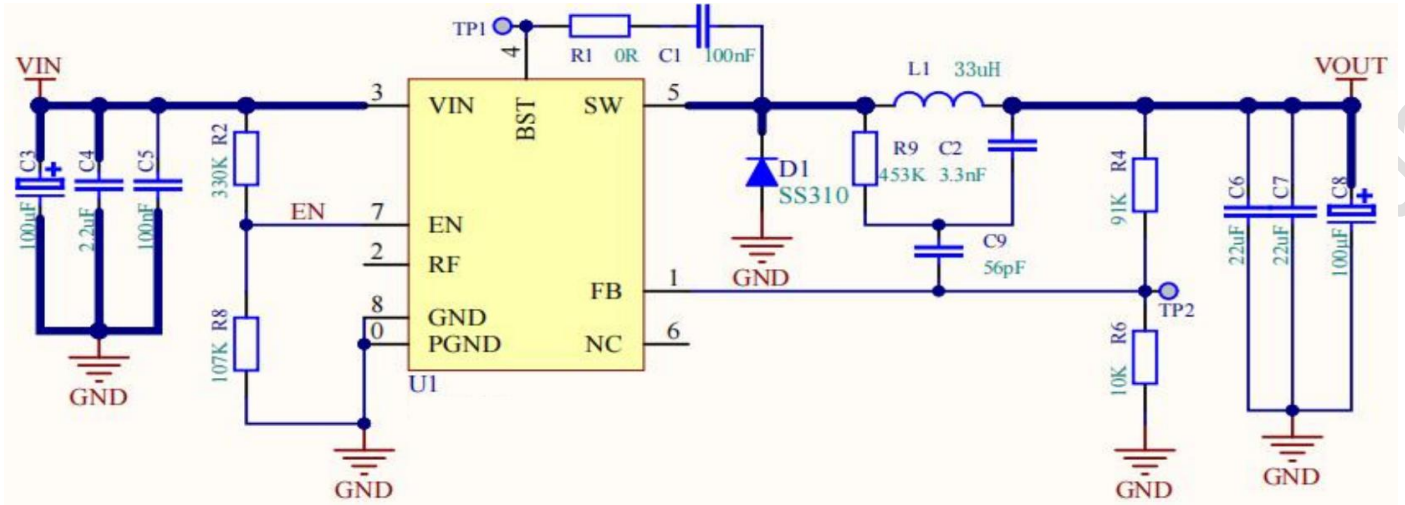


Fig. Schematic_1

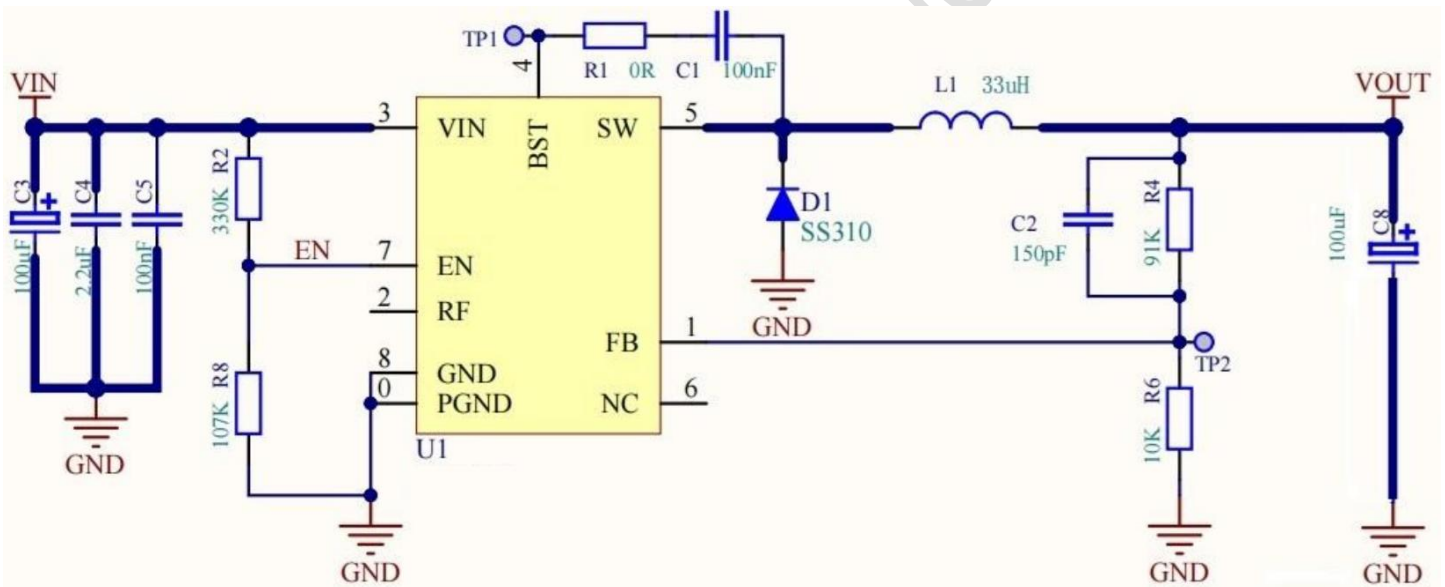
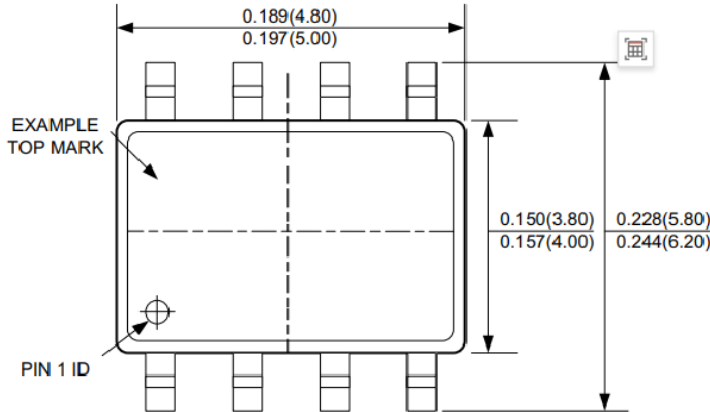


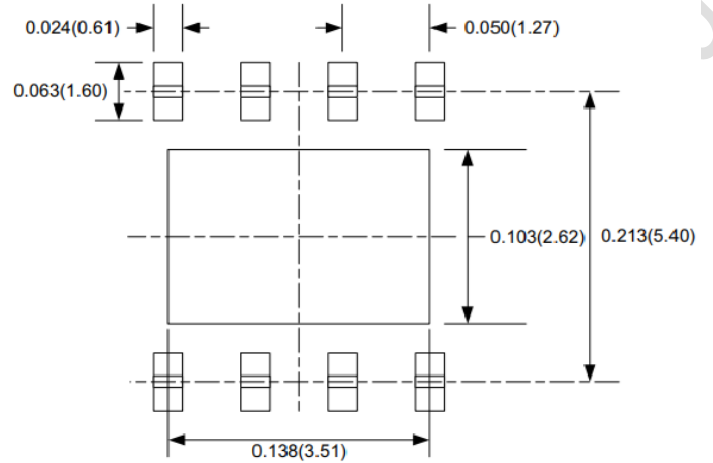
Fig. Schematic_2

PACKAGE DIMENSION

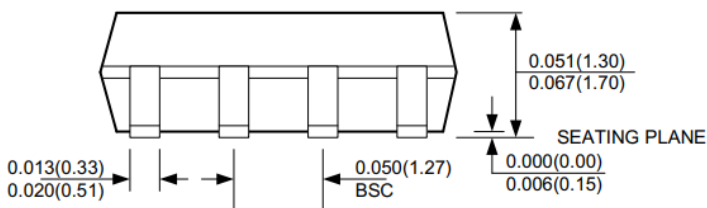
ESOP8 (EXPOSED PAD)



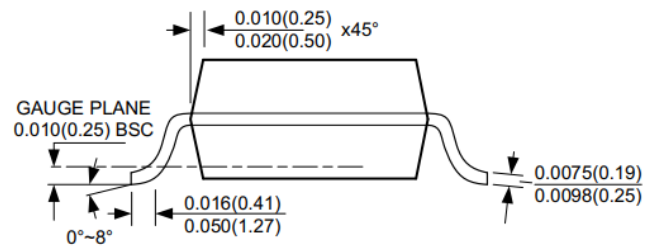
TOP VIEW



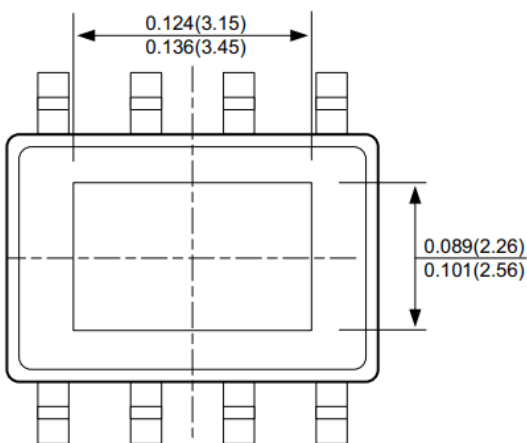
RECOMMENDED PAD LAYOUT



FRONT VIEW



SIDE VIEW



BOTTOM VIEW

NOTE:

- CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.
- DRAWING IS NOT TO SCALE.



REVISION HISTORY

Editions	Revised Date	Redaction person	Revision content
A.0	2023/12/23	PXB	First release

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